

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	16mΩ@10V	57A

Feature

- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Suffix "-Q1" for AEC-Q101

Application

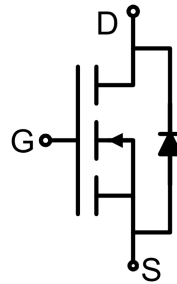
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Package

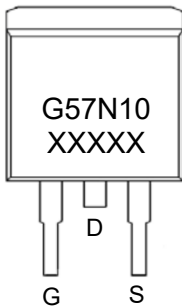


TO-263AB

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	57	A
Pulsed Drain Current	I_{DM}	190	A
Power Dissipation	P_D	170	W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.88	°C/W
Single pulse avalanche energy	E_{AS}	580	mJ
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Electrical characteristics (T_A=25 °C, unless otherwise noted)

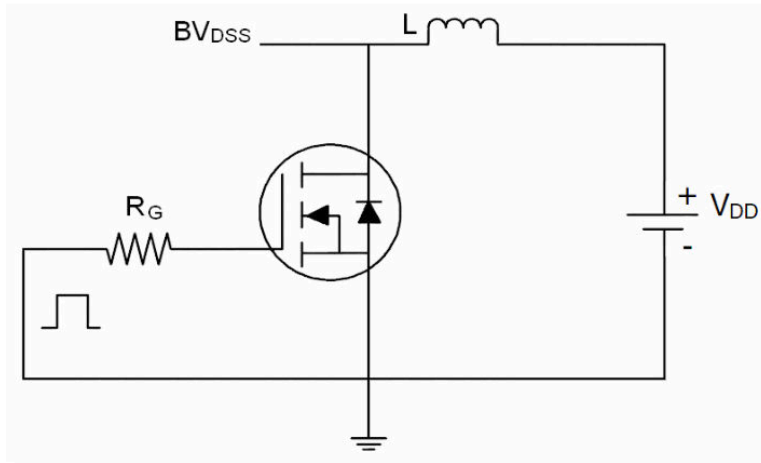
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2		4	V
Drain-source on-resistance ¹⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 28A$		12	16	mΩ
Forward transconductance ¹⁾	g_{FS}	$V_{DS} = 25V, I_D = 28A$	32			S
Dynamic characteristics²⁾						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		4400		pF
Output Capacitance	C_{oss}			320		
Reverse Transfer Capacitance	C_{rss}			240		
Total Gate Charge	Q_g	$V_{DS} = 80V, V_{GS} = 10V, I_D = 28A$		95		nC
Gate-Source Charge	Q_{gs}			18		
Gate-Drain Charge	Q_{gd}			25		
Turn-on delay time	$t_{d(on)}$	$V_{DS} = 50V, V_{GS} = 10V, I_D = 28A, R_{GEN} = 2.5\Omega$		12		nS
Turn-on rise time	t_r			55		
Turn-off delay time	$t_{d(off)}$			45		
Turn-off fall time	t_f			47		
Source-Drain Diode characteristics						
Diode Forward Current ¹⁾	I_S				57	A
Diode Forward voltage	V_{DS}	$V_{GS} = 0V, I_S = 28A$			1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = 28A$		36		nS
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s$ ¹⁾		57		nC

Notes:

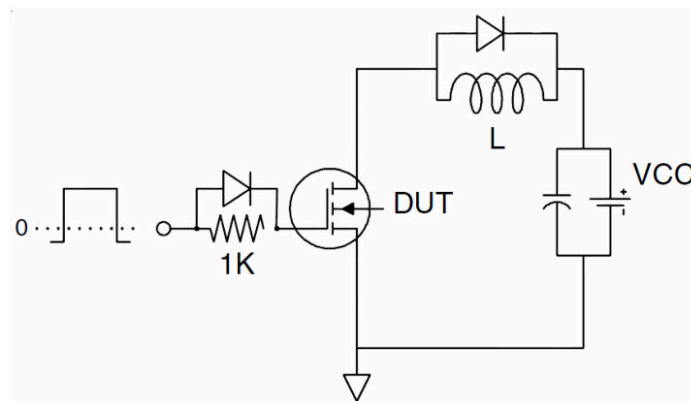
- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤ 2%.
- 2) Guaranteed by design, not subject to production testing.

Test Circuit

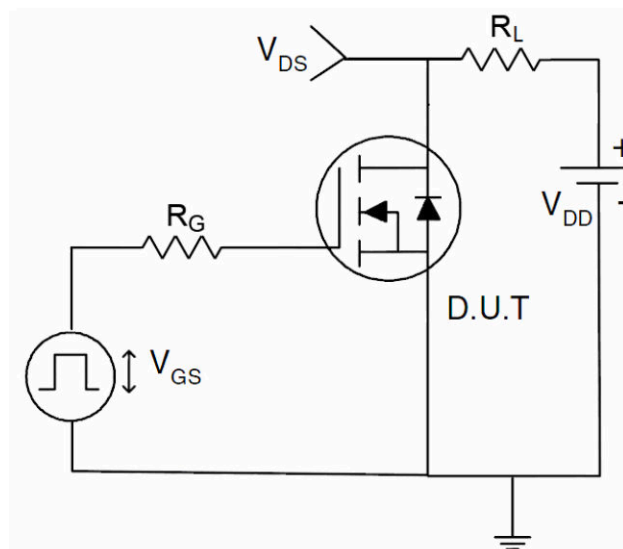
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Test Circuits and Waveforms

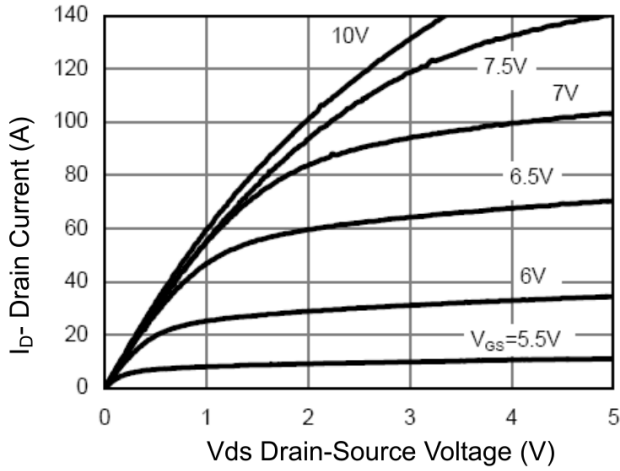


Figure 1 Output Characteristics

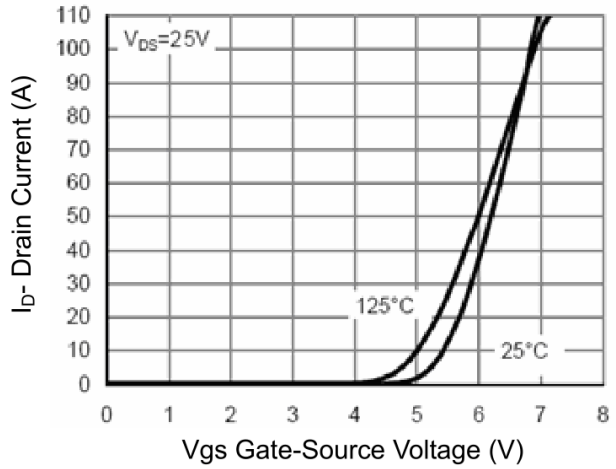


Figure 2 Transfer Characteristics

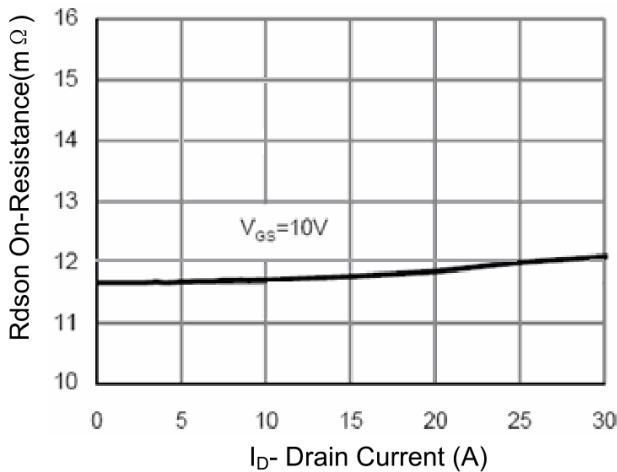


Figure 3 $R_{DS(on)}$ - Drain Current

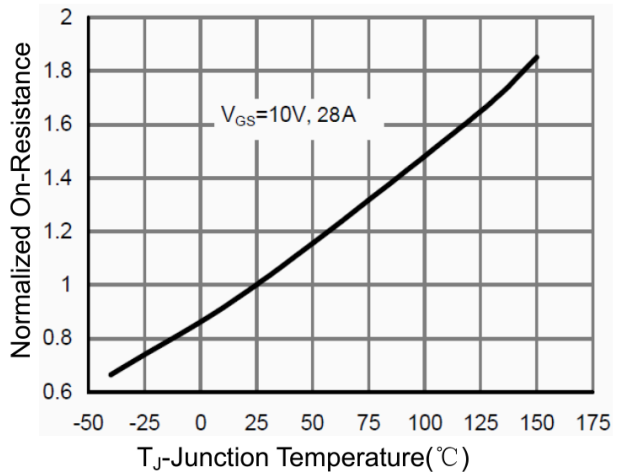


Figure 4 $R_{DS(on)}$ -Junction Temperature

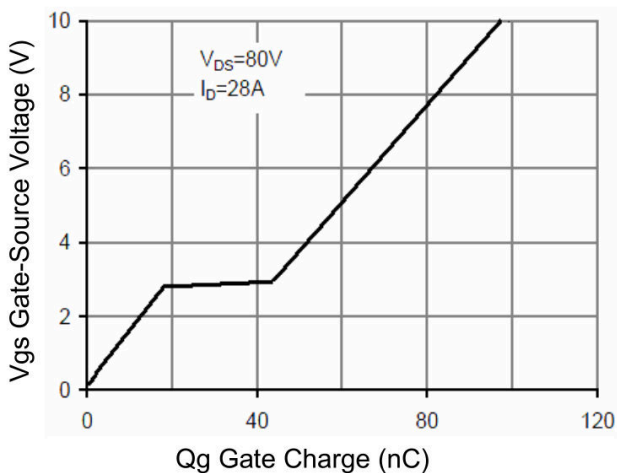


Figure 5 Gate Charge

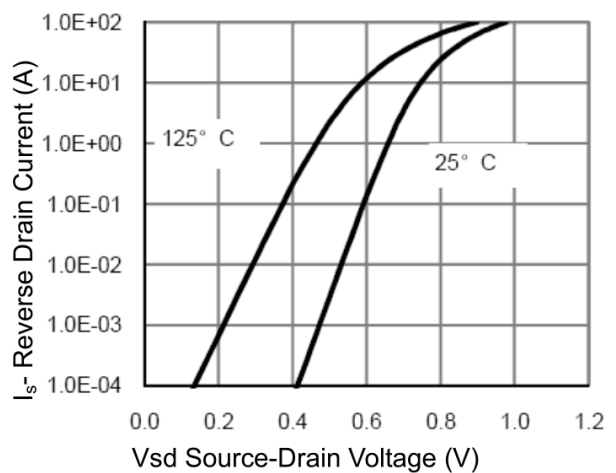


Figure 6 Source- Drain Diode Forward

Typical Characteristics

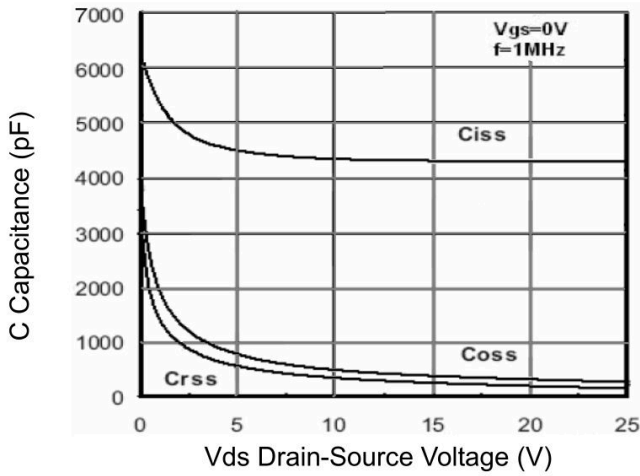


Figure 7 Capacitance vs Vds

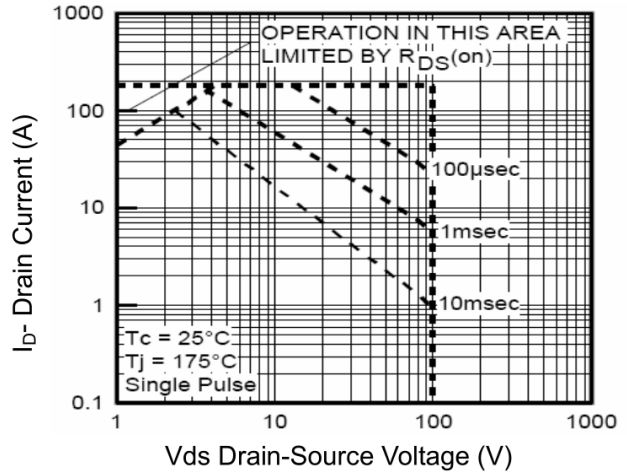


Figure 8 Safe Operation Area

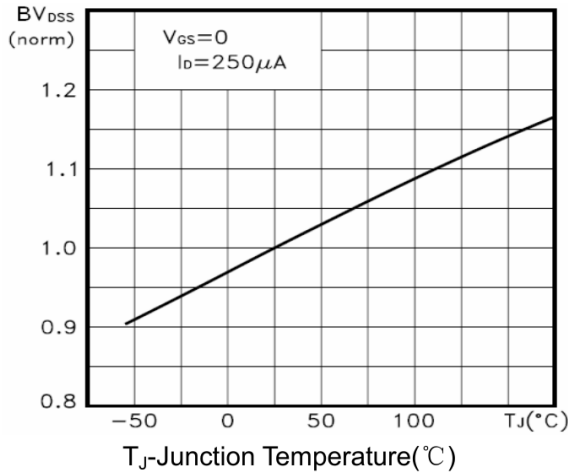


Figure 9 BV_{DSS} vs Junction Temperature

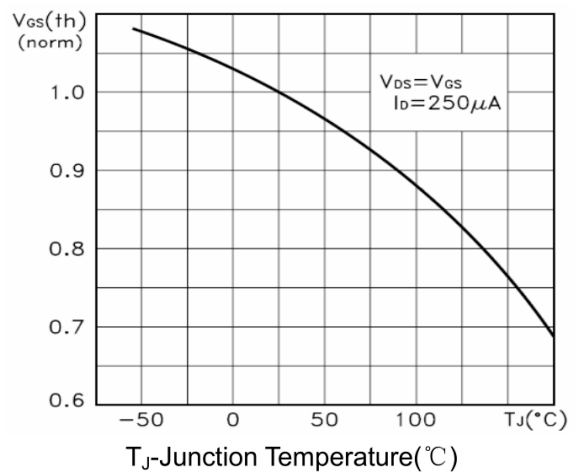
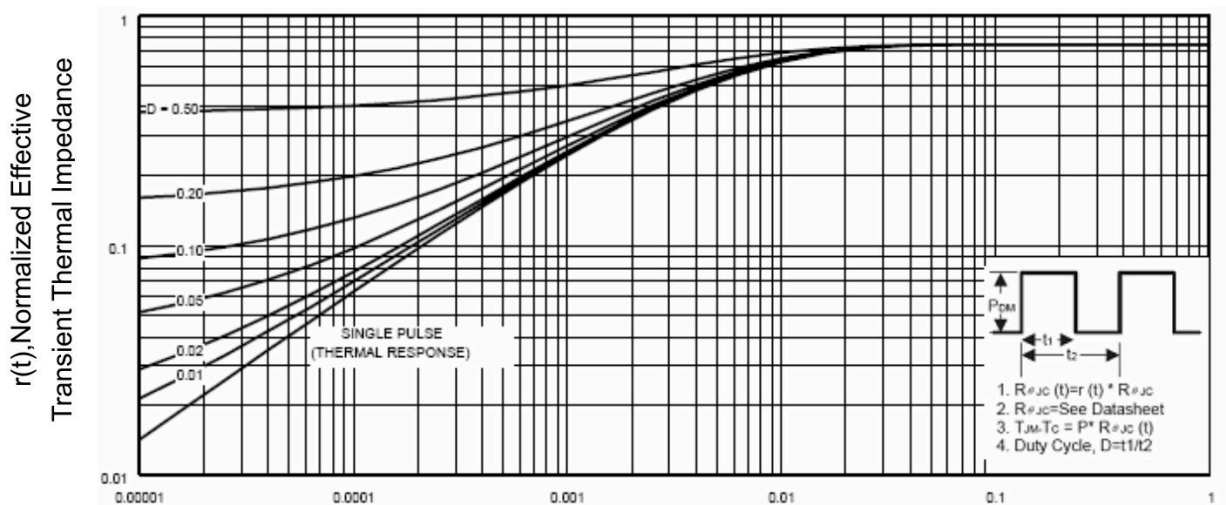


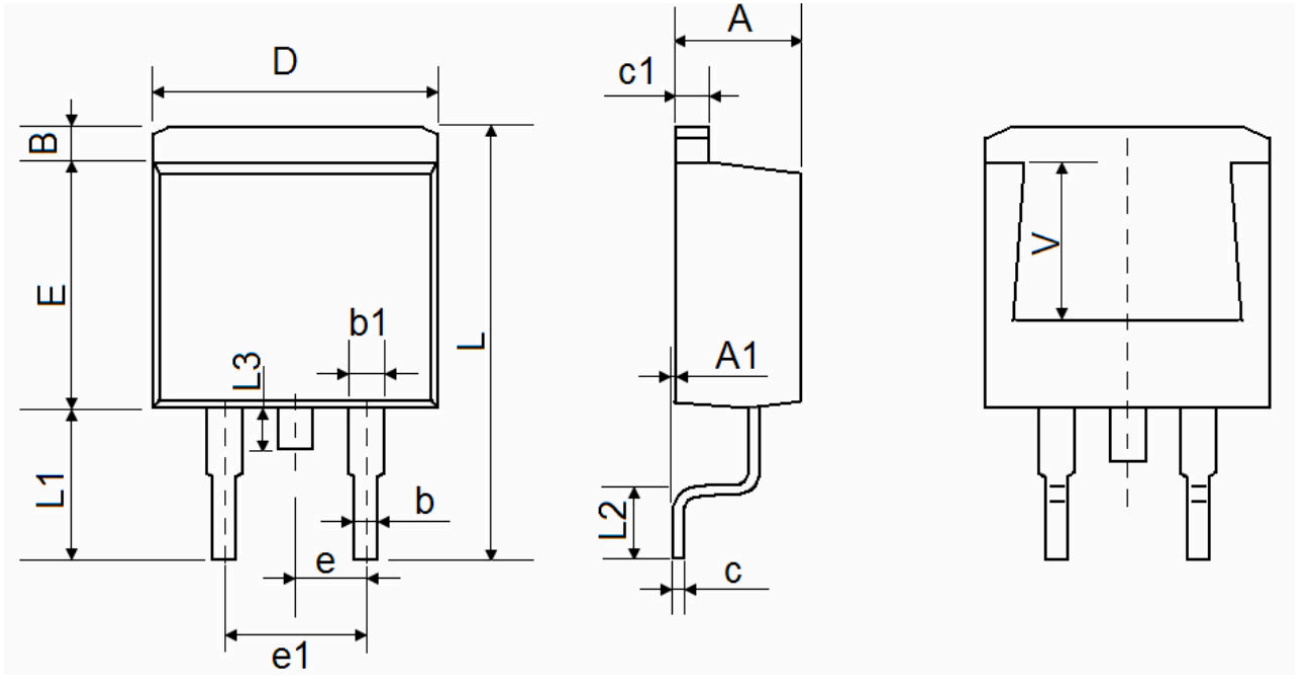
Figure 10 $V_{GS(th)}$ vs Junction Temperature



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF.		0.220 REF.	